

**GENERAL PURPOSE SILICON DIODES
METALLURGICALLY BONDED**

MAXIMUM RATINGS

Operating Temperature: -65°C to +175°C
Storage Temperature: -65°C to +175°C
Operating Current: 200 mA
Derating: 1.2 mA/°C From 25°C to 150°C
1.0 mA/°C From 150°C to 175°C
Forward Current: 650 mA

ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified

TYPE	V _{RM}	V _{RWM}	I _O	I _O	I _{FSM}
	V (pk)	V (pk)	mA	mA	A
1N5194	80	70	200	50	2
1N5195	180	180	200	60	2
1N5196	250	225	200	50	2

TYPE	V _F	I _{R1} at V _{RWM}	I _{R2} at V _{RM}	I _{R3} at V _{RWM}
	@100mA	T _A = 25°C	T _A = 25°C	T _A = 150°C
	V dc	nA dc	µA	µA dc
1N5194	0.8 - 1.0	25	100	5
1N5195	0.8 - 1.0	25	100	5
1N5196	0.8 - 1.0	25	100	5

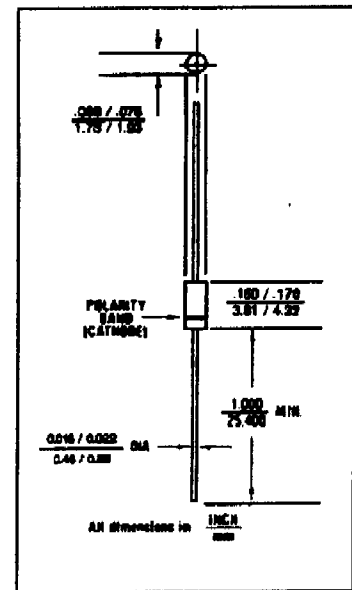


FIGURE 1

DESIGN DATA

CASE: Hermetically sealed glass case, DO - 35 outline.

LEAD MATERIAL: Copper clad steel.

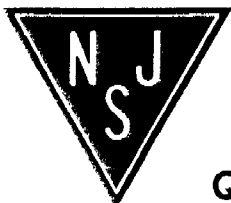
LEAD FINISH: Tin / Lead

THERMAL RESISTANCE: (R_{QJEC}): 250 °C/W maximum

THERMAL IMPEDANCE: (Z_{QJX}): 70 °C/W maximum

POLARITY: Cathode end is banded.

MOUNTING POSITION: ANY.



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